

Vishay Siliconix

COMPLIANT

Precision 8-Ch/Dual 4-Ch Low Voltage Analog Multiplexers

DESCRIPTION

The DG408L, DG409L are low voltage pin-for-pin compatible companion devices to the industry standard DG408, DG409 with improved performance.

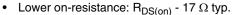
Using BiCMOS wafer fabrication technology allows the DG408L, DG409L to operate on single and dual supplies. Single supply voltage ranges from 3 V to 12 V while dual supply operation is recommended with \pm 3 V to \pm 6 V.

The DG408L is an 8 channel single-ended analog multiplexer designed to connect one of eight inputs to a common output as determined by a 3 bit binary address (A $_0$, A $_1$, A $_2$). The DG409L is a dual 4 channel differential analog multiplexer designed to connect one of four differential inputs to a common dual output as determined by its 2 bit binary address (A $_0$, A $_1$). Break-before-make switching action to protect against momentary crosstalk between adjacent channels.

The DG408L, DG409L provides lower on-resistance, faster switching time, lower leakage, less power consumption and higher off-Isolation than the DG408, DG409.

FEATURES

- Pin-for-pin compatibility with DG408, DG409
- 2.7 V to 12 V single supply or ± 3 V to ± 6 V dual supply operation



- Fast switching: ton 38 ns, tof 18 ns
- Break-before-make guaranteed
- Low leakage: I_{S(off)} 0.2 nA max.
- Low charge injection: 1 pC
- TTL, CMOS, LV logic (3 V) compatible
- 82 dB off-isolation at 1 MHz
- 2000 V ESD protection (HBM)
- Compliant to RoHS directive 2002/95/EC

BENEFITS

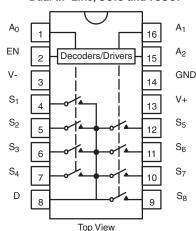
- · High accuracy
- Single and dual power rail capacity
- · Wide operating voltage range
- · Simple logic interface

APPLICATIONS

- Data acquisition systems
- · Battery operated equipment
- · Portable test equipment
- Sample and hold circuits
- Communication systems
- SDSL, DSLAM
- Audio and video signal routing

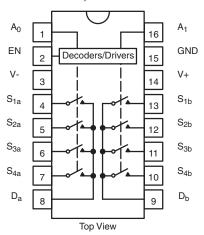
FUNCTIONAL BLOCK DIAGRAMS AND PIN CONFIGURATIONS

DG408L Dual-In- Line, SOIC and TSSOP



DG409L

Dual-In- Line, SOIC and TSSOP



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^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

DG408L, DG409L

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TRUTI	H TABLE	■ DG408L	-					
A ₂	A ₁	Α ₀	EN On Switch					
Х	Х	Х	0	None				
0	0	0	1	1				
0	0	1	1	2				
0	1	0	1	3				
0	1	1	1	4				
1	0	0	1	5				
1	0	1	1	6				
1	1	0	1	7				
1	1	1	1	8				

TRUTH	TABLE DO	3409L	
A ₁	A ₀	EN	On Switch
Х	Х	0	None
0	0	1	1
0	1	1	2
1	0	1	3
1	1	1	4

Logic "0" = $V_{AL} \le 0.8 \text{ V}$ Logic "1" = $V_{AH} \ge 2.4 \text{ V}$ X = Do not Care

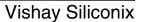
For low and high voltage levels for V_{AX} and V_{EN} consult "Digital Control" parameters for specific V+ operation.

ORDERING	ORDERING INFORMATION DG408L					
Temp. Range	Package	Part Number				
- 40 °C to 85 °C	16-Pin SOIC	DG408LDY DG408LDY-E3 DG408LDY-T1 DG408LDY-T1-E3				
- 40 0 10 85 0	16-Pin TSSOP	DG408LDQ DG408LDQ-E3 DG408LDQ-T1 DG408LDQ-T1-E3				

ORDERING I	NFORMATION [DG409L
Temp. Range	Package	Part Number
- 40 °C to 85 °C	16-Pin SOIC	DG409LDY DG409LDY-E3 DG409LDY-T1 DG409LDY-T1-E3
- 40 0 10 65 0	16-Pin TSSOP	DG409LDQ DG409LDQ-E3 DG409LDQ-T1 DG409LDQ-T1-E3

ABSOLUTE MAXIMUM RA	TINGS			
Parameter		Limit	Unit	
Voltage Referenced V+ to V-		14		
GND		7	V	
Digital Inputs ^a , V _S , V _D		(V-) - 0.3 to (V) + 0.3		
Current (Any Terminal)		30	mA	
Peak Current, S or D (Pulsed at 1 ms,	10 % Duty Cycle Max.)	100	IIIA	
eak Current, S or D (Pulsed at 1 ms, 1) orage Temperature	(A Suffix)	- 65 to 150	°C	
Storage remperature	(D Suffix)	14 7 (V-) - 0.3 to (V) + 0.3 30 100 - 65 to 150 - 65 to 125 650 600 900		
	16-Pin Plastic TSSOP ^c	650		
Device Dissipation (Dealers)	16-Pin Narrow SOIC ^c	600	mW	
Power Dissipation (Package) ^b	16-Pin CerDIP ^d	900	11100	
	LCC-20 ^e	750		

- $a. \ Signals \ on \ S_X, \ DX, \ A_X, \ or \ EN \ exceeding \ V+ \ or \ V- \ will \ be \ clamped \ by \ internal \ diodes. \ Limit \ forward \ diode \ current \ to \ maximum \ current \ ratings.$
- b. All leads soldered or welded to PC board.
- c. Derate 7.6 mW/°C above 75 °C.
- d. Derate 12 mW/°C above 75 °C.
- e. Derate 10 mW/°C above 75 °C.





SPECIFICATIONS	T T	1	I	l				***	
		Test Conditions Unless Otherwise Specified				uffix o 125°C		uffix	
		V+ = 12 V, ± 10 %, V- = 0 V			- 33 01	123 0	-40 0	10 03 0	
Parameter	Symbol	$V_{EN} = 0.8 \text{ V or } 2.4 \text{ V}^{f}$	Temp.b	Typ. ^d	Min.c	Max.c	Min.c	Max.c	Unit
Analog Switch			•				<u> </u>		
Analog Signal Range ^e	V _{ANALOG}		Full		0	12	0	12	V
Drain-Source On-Resistance	R _{DS(on)}	$V_D = 10.8 \text{ V}, V_D = 2 \text{ V or 9 V}, I_S = 10 \text{ mA}$ Sequence Each Switch On	Room Full	17		29 38		29 35	
R _{DS(on)} Matching Between Channels ^g	ΔR _{DS}	$V_D = 10.8 \text{ V}, V_D = 2 \text{ V or 9 V}$ $I_S = 10 \text{ mA}$	Room	1		3		3	Ω
On-Resistance Flatness ⁱ	R _{FLAT(on)}	ig – 10 mA	Room	3		7		7	
Switch Off Leakage	I _{S(off)}	V _{EN} = 0 V, V _D = 11 V or 1 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Current	I _{D(off)}	V _S = 1 V or 11 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA
Channel On Leakage Current	I _{D(on)}	$V_{S} = V_{D} = 1 \text{ V or } 11 \text{ V}$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Digital Control		,	•	ı		•			
Logic High Input Voltage	V _{INH}		Full		2.4		2.4		V
Logic Low Input Voltage	V _{INL}		Full			0.8		0.8	
Input Current	I _{IN}	$V_{AX} = V_{EN} = 2.4 \text{ V or } 0.8 \text{ V}$	Full		- 1.5	1.5	- 1	1	μΑ
Dynamic Characteristics		,		•					
Transition Time	t _{TRANS}	$V_{S1} = 8 \text{ V, } V_{S8} = 0 \text{ V, (DG408L)}$ $V_{S1b} = 8 \text{ V, } V_{S4b} = 0 \text{ V, (DG409L)}$ See Figure 2	Room Full	30		60 68		60 65	
Break-Before-Make Time	t _{OPEN}	$V_{S(all)} = V_{DA} = 5 V$ See Figure 4	Room Full	11	1		1		ns
Enable Turn-On Time	t _{ON(EN)}	V _{AX} = 0 V, V _{S1} = 5 V (DG408L) V _{AX} = 0 V, V _{S1b} = 5 V (DG409L)	Room Full	38		55 60		55 60	
Enable Turn-Off Time	t _{OFF(EN)}	See Figure 3	Room Full	18		25 35		25 30	
Charge Injection ^e	Q	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega$	Room	1		5		5	рC
Off Isolation ^{e, h}	OIRR	$f = 100 \text{ kHz}, R_L = 1 \text{ k}\Omega$	Room	- 70					dB
Crosstalk ^e	X _{TALK}	1 = 100 KHZ, HE = 1 KSZ	Room	- 82					uБ
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz, V _S = 0 V, V _{EN} = 0 V	Room	7					
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz, V _D = 2.4 V, V _{EN} = 0 V	Room	20					рF
Drain On Capacitance ^e	C _{D(on)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{EN} = 2.4 \text{ V}$ (DG409L only)	Room	31					ρı
Power Supplies									
Power Supply Range	V+				3	12	3	12	V
Power Supply Current	I+	$V_{EN} = V_A = 0 \text{ V or 5 V}$	Room	0.2		0.7		0.7	mA

- a. Leakage parameters are guaranteed by worst case test condition and not subject to production test.
- b. Room = 25 $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- e. Guaranteed by design, not subject to production test. f. V_{IN} = input voltage to perform proper function.

- g. $\Delta R_{DS(on)} = R_{DS(on)} Max R_{DS(on)} Min$. h. Worst case isolation occurs on Channel 4 do to proximity to the drain pin.
- i. R_{DS(on)} flatness is measured as the difference between the minimum and maximum measured values across a defined Analog signal.

DG408L, DG409L

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SPECIFICATIONS	Dual Sup	oply V+ = 5 V, V = 5 V							
		Test Conditions				uffix o 125 °C	_	uffix	
		Unless Otherwise Specified V+ = 5 V, ± 10 %, V- = - 5 V, V- = 0 V			- 55 °C to	0 125 °C	- 40 °C	10 85 0	•
Parameter	Symbol	V _{EN} = 0.6 V or 2.4 V ^f	Temp.b	Typ.d	Min.c	Max.c	Min.c	Max.c	Unit
Analog Switch				, ,.		L			
Analog Signal Range ^e	V _{ANALOG}		Full		- 5	5	- 5	5	V
Drain-Source On-Resistance	R _{DS(on)}	$V_D = \pm 3.5 \text{ V}, I_S = 10 \text{ mA}$ Sequence Each Switch On	Room Full	20		40 50		40 50	Ω
Switch Off Leakage	I _{S(off)}	V+ = 5.5 , V- = 5.5 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Current ^a	I _{D(off)}	$V_{EN} = 0 \text{ V}, V_{D} = \pm 4.5 \text{ V}, V_{S} = 4.5 \text{ V}$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA
Channel On Leakage Current ^a	I _{D(on)}	V+ = 5.5 V, V- = -5.5 V $V_{EN} = 2.4 \text{ V}, V_D = \pm 4.5 \text{ V}, V_S = 4.5 \text{ V}$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Digital Control		Ŧ							
Logic High Input Voltage	V _{INH}		Full		2.4		2.4		V
Logic Low Input Voltage	V _{INL}		Full			0.6		0.6	
Input Current ^a	I _{IN}	$V_{AX} = V_{EN} = 2.4 \text{ V or } 0.6 \text{ V}$	Full		- 1.5	1.5	- 1	1	μΑ
Dynamic Characteristics				1					
Transition Time ^e	t _{TRANS}	$V_{S1} = 3.5 \text{ V}, V_{S8} = -3.5 \text{ V}, (DG408L)$ $V_{S1b} = 3.5 \text{ V}, V_{S4b} = -3.5 \text{ V}, (DG409L)$ See Figure 2	Room Full	30		60 78		60 65	
Break-Before-Make Time ^e	t _{OPEN}	$V_{S(all)} = V_{DA} = 3.5 \text{ V}$ See Figure 4	Room Full	8	1		1		ns
Enable Turn-On Time ^e	t _{ON(EN)}	V _{AX} = 0 V, V _{S1} = 3.5 V (DG408L) V _{AX} = 0 V, V _{S1b} = 3.5 V (DG409L)	Room Full	25		55 68		55 60	
Enable Turn-Off Time ^e	t _{OFF(EN)}	See Figure 3	Room Full	20		40 50		40 45	
Source Off Capacitance ^e	C _{S(off)}	$f = 1 \text{ MHz}, V_S = 0 \text{ V}, V_{EN} = 0 \text{ V}$	Room	6					
Drain Off Capacitance ^e	C _{D(off)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{EN} = 0 \text{ V}$	Room	15					рF
Drain On Capacitance ^e	C _{D(on)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{EN} = 2.4 \text{ V}$	Room	29			_		

- a. Leakage parameters are guaranteed by worst case test condition and not subject to production test.
- b. Room = 25 °C, full = as determined by the operating temperature suffix.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- d. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.
- g. $\Delta R_{DS(on)} = R_{DS(on)}$ max. $R_{DS(on)}$ min. h. Worst case isolation occurs on channel 4 do to proximity to the drain pin.
- i. R_{DS(on)} flatness is measured as the difference between the minimum and maximum measured values across a defined analog signal.





SPECIFICATIONS	Single Su								
		Test Conditions Unless Otherwise Specified				uffix o 125°C	_	uffix to 85 °C	
		$V + = 5 \text{ V}, \pm 10 \%, V - = 0 \text{ V}$			- 33 01	123 0	-40 0	0000	
Parameter	Symbol	$V_{EN} = 0.6 \text{ V or } 2.4 \text{ V}^{f}$	Temp.b	Typ.d	Min.c	Max.c	Min.c	Max.c	Uni
Analog Switch						L		L	
Analog Signal Range ^e	V _{ANALOG}		Full		0	5	0	5	٧
Drain-Source On-Resistance	R _{DS(on)}	$V+ = 4.5 \text{ V}, V_D \text{ or } V_S = 1 \text{ V or } 3.5 \text{ V},$ $I_D = 5 \text{ mA}$	Room Full	35		49 62		40 62	
R _{DS(on)} Matching Between Channels ^g	ΔR_{DS}	$V+ = 4.5 \text{ V}, V_D = 1 \text{ V or } 3.5 \text{ V},$	Room	1.5		3		3	Ω
On-Resistance Flatness ⁱ	R _{FLAT(on)}	$I_S = 5 \text{ mA}$	Room			4		4	
Switch Off Leakage	I _{S(off)}	V+ = 5.5 V, V _S = 1 V or 4 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Current ^a	I _{D(off)}	$V_D = 4 V \text{ or } 1 V$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA
Channel On Leakage Current ^a	I _{D(on)}	$V+ = 5.5 V$, $V_D = V_S = 1 V$ or 4 V Sequence Each Switch On	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Digital Control									
Logic High Input Voltage	V_{INH}	V+ = 5 V	Full		2.4		2.4		V
Logic Low Input Voltage	V_{INL}		Full			0.6		0.6	٧
Input Current ^a	I _{IN}	$V_{AX} = V_{EN} = 2.4 \text{ V or } 0.6 \text{ V}$	Full		- 1.5	1.5	- 1	1	μΑ
Dynamic Characteristics									
Transition Time ^e	t _{TRANS}	$V_{S1} = 3.5 \text{ V}, V_{S8} = 0 \text{ V}, (DG408L)$ $V_{S1b} = 3.5 \text{ V}, V_{S4b} = 0 \text{ V}, (DG409L)$ See Figure 2	Room Full	44		125 138		125 135	
Break-Before-Make Time ^e	t _{OPEN}	$V_{S(all)} = V_{DA} = 3.5 \text{ V},$ See Figure 4	Room Full	17	1		1		ns
Enable Turn-On Time ^e	t _{ON(EN)}	$V_{AX} = 0 \text{ V}, V_{S1} = 3.5 \text{ V (DG408L)}$ $V_{AX} = 0 \text{ V}, V_{S1b} = 3.5 \text{ V (DG409L)}$	Room Full	43		60 70		60 65	
Enable Turn-Off Time ^e	t _{OFF(EN)}	See Figure 3	Room Full	26		45 60		45 50	
Charge Injection ^e	Q	C_L = 1 nF, R_{GEN} = 0 Ω , V_{GEN} = 0 Ω	Room	1		5		5	рС
Off Isolation ^{e, h}	OIRR	$f = 100 \text{ kHz}, R_1 = 1 \text{ k}\Omega$	Room	- 70					dB
Crosstalk ^e	X _{TALK}	1 – 100 M12, 11 <u>L</u> – 1 M22	Room	- 80					ub
Source Off Capacitance ^e	C _{S(off)}	$f = 1 \text{ MHz}, V_S = 0 \text{ V}, V_{EN} = 0 \text{ V}$	Room	8					
Drain Off Capacitance ^e	C _{D(off)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{EN} = 0 \text{ V}$	Room	21					рF
Drain On Capacitance ^e	C _{D(on)}	f = 1 MHz, V _D = 0 V, V _{EN} = 2.4 V (DG409L only)	Room	32					Pr

Notes:

- a. Leakage parameters are guaranteed by worst case test condition and not subject to production test.
- b. Room = 25 °C, full = as determined by the operating temperature suffix.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- d. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.
- g. $\Delta R_{DS(on)} = R_{DS(on)}$ max. $R_{DS(on)}$ min. h. Worst case isolation occurs on channel 4 do to proximity to the drain pin.
- i. R_{DS(on)} flatness is measured as the difference between the minimum and maximum measured values across a defined analog signal.

DG408L, **DG409L**

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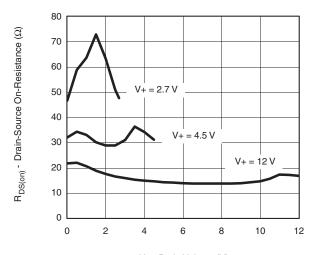
SPECIFICATIONS	Single Su	pply 3 V							
		Test Conditions Unless Otherwise Specified V+ = 3 V, ± 10 %, V- = 0 V			A Suffix - 55 °C to 125 °C		D Suffix - 40 °C to 85 °C		
Parameter	Symbol	$V_{EN} = 0.4 \text{ V or } 2.0 \text{ V}^{f}$	Temp.b	Typ.d	Min.c	Max.c	Min.c	Max.c	Unit
Analog Switch	-					L		·	
Analog Signal Range ^e	V _{ANALOG}		Full		0	3	0	3	V
Drain-Source On-Resistance	R _{DS(on)}	$V+ = 2.7 \text{ V}, V_D = 0.5 \text{ or } 2.2 \text{ V},$ $I_S = 5 \text{ mA}$	Room Full	60		80 105		80 100	Ω
Switch Off Leakage	I _{S(off)}	V+ = 3.3 V, V _S = 2 or 1 V, V _D = 1 or 2 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Current ^a	I _{D(off)}	V = 0.0 V, VS = 2 0.1 V, VB = 1 0.1 2 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA
Channel On Leakage Current ^a	I _{D(on)}	$V+ = 3.3 \text{ V}, V_D = V_S = 1 \text{ or } 2 \text{ V}$ Sequence Each Switch On	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Digital Control									
Logic High Input Voltage	V_{INH}		Full		2		2		٧
Logic Low Input Voltage	V_{INL}		Full			0.4		0.4	V
Input Current ^a	I _{IN}	$V_{AX} = V_{EN} = 2.4 \text{ V or } 0.4 \text{ V}$	Full		- 1.5	1.5	- 1	1	μΑ
Dynamic Characteristics									
Transition Time	t _{TRANS}	$V_{S1} = 1.5 \text{ V}, V_{S8} = 0 \text{ V}, (DG408L)$ $V_{S1b} = 1.5 \text{ V}, V_{S4b} = 0 \text{ V}, (DG409L)$ See Figure 2	Room Full	75		150 175		150 175	
Break-Before-Make Time	t _{OPEN}	V _{S(all)} = V _{DA} = 1.5 V, See Figure 4	Room Full	32	1		1		ns
Enable Turn-On Time	t _{ON(EN)}	V _{AX} = 0 V, V _{S1} = 1.5 V (DG408L) V _{AX} = 0 V, V _{S1b} = 1.5 V (DG409L)	Room Full	70		95 115		95 105	
Enable Turn-Off Time	t _{OFF(EN)}	See Figure 3	Room Full	55		100 115		100 105	
Charge Injection ^e	Q	$C_L = 1 \text{ nF, } R_{GEN} = 0 \Omega, V_{GEN} = 0 V$	Room	0.4		5		5	рC
Off Isolation ^{e, h}	OIRR	R _I = 1 kΩ, f = 100 kHz	Room	- 70					dB
Crosstalk ^e	X _{TALK}	1 11 = 1 K22, 1 = 100 K112	Room	- 79					uB
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz, V _S = 0 V, V _{EN} = 0 V	Room	8					
Drain Off Capacitance ^e	C _{D(off)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{EN} = 0 \text{ V}$	Room	19					рF
Drain On Capacitance ^e	C _{D(on)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{EN} = 2 \text{ V}$ (DG409L only)	Room	33					۲,

- a. Leakage parameters are guaranteed by worst case test condition and not subject to production test.
- b. Room = $25 \, ^{\circ}$ C, full = as determined by the operating temperature suffix.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- d. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.
- g. $\Delta R_{DS(on)} = R_{DS(on)}$ max. $R_{DS(on)}$ min. h. Worst case isolation occurs on channel 4 do to proximity to the drain pin.
- i. R_{DS(on)} flatness is measured as the difference between the minimum and maximum measured values across a defined analog signal.

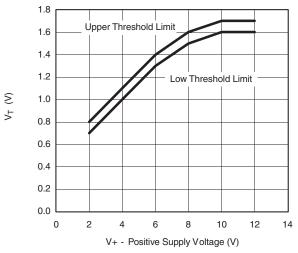
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



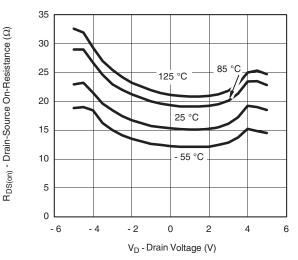
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



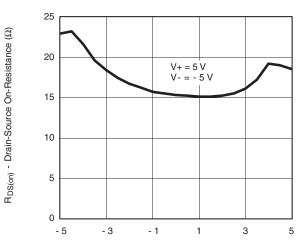
 $\label{eq:VD-D} V_D \text{ - Drain Voltage (V)} \\ \textbf{R}_{\textbf{DS(on)}} \ \textbf{vs. V}_{\textbf{D}} \ \textbf{and Power Supply}$



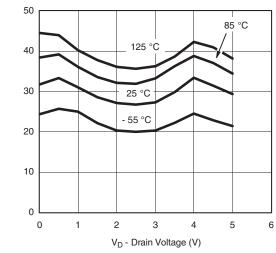
Input Threshold vs. V+ Supply Voltage



 $R_{DS(on)}$ vs. V_D and Temperature



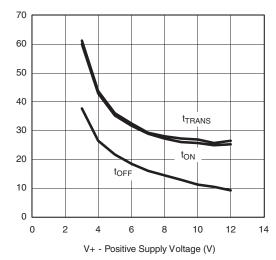
 V_D - Drain Voltage (V) $\mathbf{R_{DS(on)}}$ vs. V_D and Power Supply



 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain-Source On-Resistance (Ω)

Switching Speed (nS)

R_{DS(on)} vs. V_D and Temperature

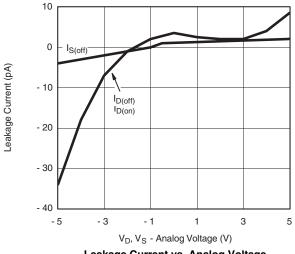


Switching Time vs. Positive Supply Voltage

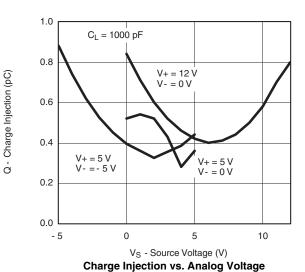
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Leakage Current vs. Analog Voltage



35
30
25
V+ = 12 V
V- = 0 V
20
CD(off)
15
CS(off)
5
Drain/Source Capacitance vs. Analog Voltage

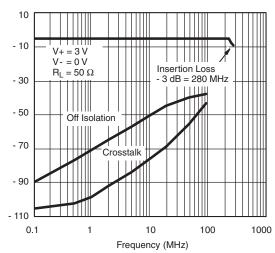
40 35 30 ton 25 t_{TRANS} 20 toff 15 10 5 0 5 6 3 ± - Dual Power Supply Voltage (V)

Switching Speed (nS)

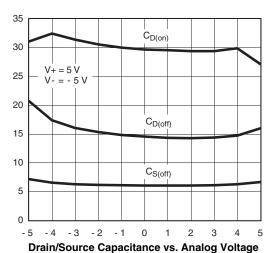
Loss (dB)

C_D, C_S - Drain/Source Capacitance (pF)

Switching Time vs. Dual Power Supply Voltage



Insertion Loss, Off Isolation and Crosstalk vs. Frequency (Single Supply)



C_D, C_S - Drain/Source Capacitance (pF)



SCHEMATIC DIAGRAM Typical Channel

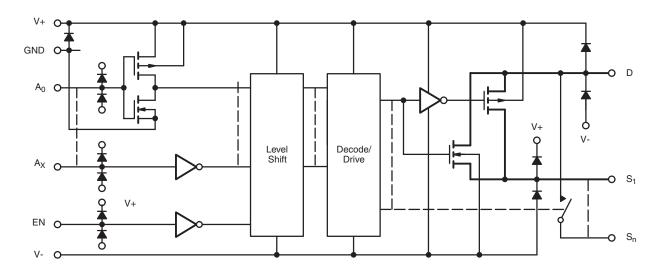


Figure 1.

TEST CIRCUITS

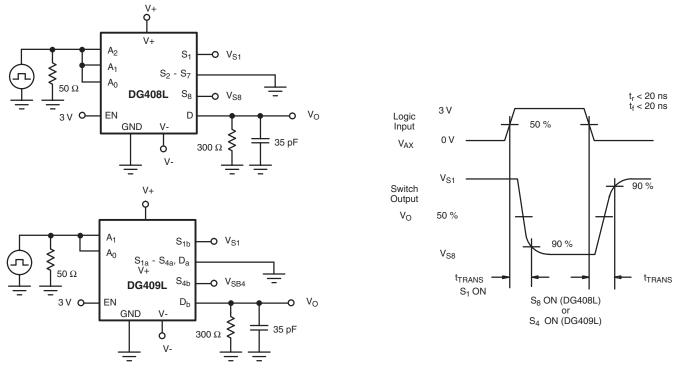


Figure 2. Transition Time

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TEST CIRCUITS



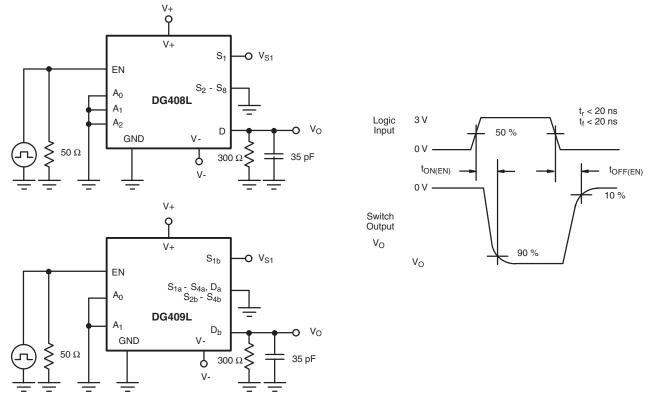


Figure 3. Enable Switching Time

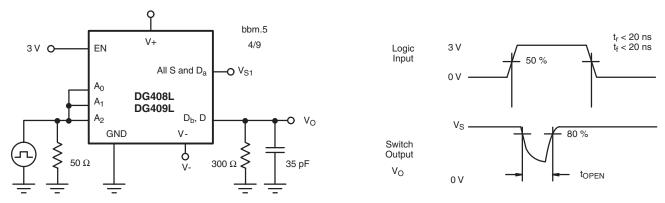


Figure 4. Break-Before-Make Interval



TEST CIRCUITS

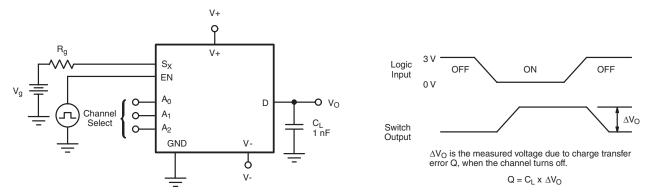


Figure 5. Charge Injection

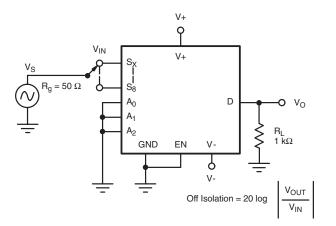


Figure 6. Off Isolation

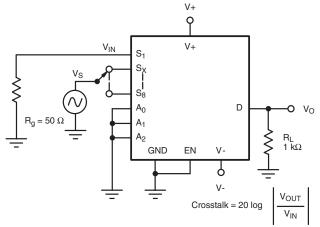


Figure 7. Crosstalk

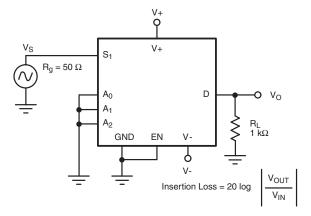


Figure 8. Insertion Loss

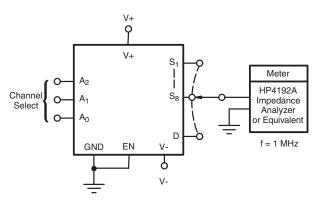


Figure 9. Source Drain Capacitance

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